

/ Descriptions

WR0596

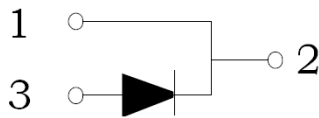
Ultrafast Recovery Diode in a TO-263 Plastic Package.

/ Features

Silicon epitaxial process to produce ultrafast recovery diode with low reverse leakage current and high reliability.

/ Applications

For high frequency, high voltage, high current rectifier diode, freewheeling diode.

/ Equivalent Circuit**/ Pinning**

PIN1 Anode

PIN 2 4 Cathode

PIN 3 Anode

/ h_{FE} Classifications & Marking

See Marking Instructions

/ Absolute Maximum Ratings(Ta=25)

Parameter	Symbol	Rating	Unit
Peak Repetitive Reverse Voltage	V_{RRM}	600	V
RMS Voltage	V_{RMS}	420	V
DC Blocking Voltage	V_{DC}	600	V
Maximum Average Forward Current	I_F	1 × 30	A
Peak forward surge current	I_{FSM}	300	A
Typical Thermal Resistance Junction to Case	$R_{\theta JC}$	2.0	/W
Junction Temperature Range	T_J	150	
Storage Temperature Range	T_{stg}	-55 150	

/ Electrical Characteristics(Ta=25)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Forward Voltage	V_F	$I_F=5.0A$ $T_C=25$			1.35	V
		$I_F=5.0A$ $T_C=150$			1.15	
		$I_F=30A$ $T_C=25$			1.65	
		$I_F=30A$ $T_C=150$			1.25	
Instantaneous Reverse Current Note1	I_R	$V_R=600V$ $T_a=25$			0.25	mA
		$V_R=420V$ $T_a=150$			1	
		$V_R=600V$ $T_a=150$			2	
Reverse Recovery Time	t_{rr}	$I_F=0.5A$ $I_R=1.0A$ $I_{RR}=0.25A$			50	ns

2Notes

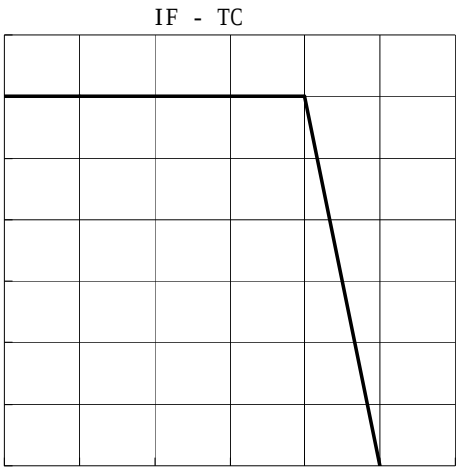
1.

2.

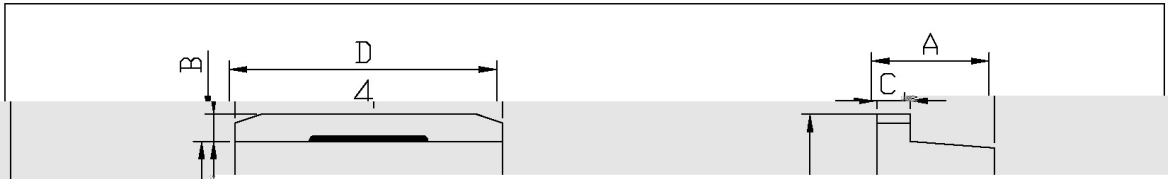
2Short duration pulse test used to minimize self-heating

2 Unless otherwise noted, values for the parameters of a

/ Electrical Characteristic Curve



/ Package Dimensions

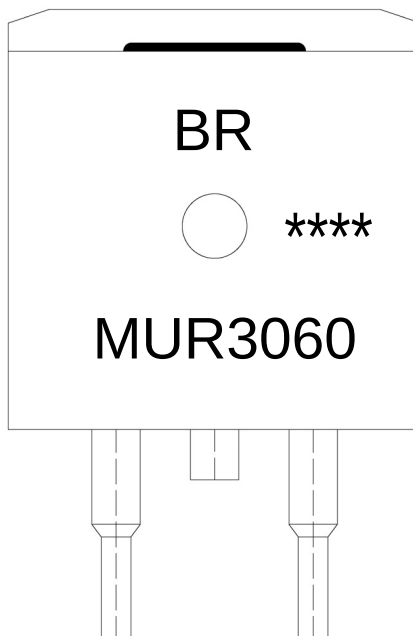


单位: mm

Dimensions In Millimeters			Dimensions In Millimeters		
Symbol	Min	Max	Symbol	Min	Max
A	4.30	4.70	E	9.00	9.40
B	1.00	1.40	e1	2.24	2.74
b	0.70	0.90	e2	4.88	5.28
b1	1.15	1.35	L1	15.00	16.00
b2	0.40	0.60	L2	2.24	2.84
C	1.20	1.40	L3	1.20	1.60
D	9.80	10.20			

TP-263

/ Marking Instructions



EU

P XU6393

Note:

BR: Company Code

MUR3060 Product Type.

****: Lot No. Code, code change with Lot No.

BRMUR3060BD

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